

Abstract

Apparatus and method for producing a doped monocrystalline rod made of silicon

5 The invention relates to an apparatus and a method for producing a doped crystal
according to the Czochralski process, comprising a pressure vessel, a crucible which
is located in the pressure vessel and can contain liquid silicon, and an apparatus for
doping the melt, containing a housing, a storage container for holding a dopant, a
conveyor belt for conveying the dopant, an apparatus for forming a packed bed on the
10 conveyor belt, and a tube, into the first end of which tube dopant from the conveyor
belt can enter and the second end of which tube points in the direction of the liquid
silicon and is closed off relative to the liquid silicon by a porous separating element.

[Fig. 1]